

AMENDMENTS TO THE CLAIMS

Please amend claims 1-5 and 13-16 as set forth below.

1. (CURRENTLY AMENDED) A semiconductor device comprising:
a semiconductor substrate;
a high-dielectric-constant film on the semiconductor substrate; and
a nitride layer on the high-dielectric-constant film,
wherein the high-dielectric constant film is selected from film comprised of enhanced dielectric materials including Al₂O₃, ZrO₂, HfO₂, and PrO₂, silicate film derived from said enhanced dielectric materials, film having multi-element materials including a combination of at least two of Al₂O₃, ZrO₂, HfO₂, and PrO₂, and film having multi-layered structures including at least two layers of said silicate film.
2. (CURRENTLY AMENDED) The semiconductor device according to claim 1, further comprising:
a p-type impurity-contained layer on the nitride layer.
3. (CURRENTLY AMENDED) The semiconductor device according to claim 1, wherein the nitride layer is formed by introducing nitrogen into a top surface portion of the high-dielectric-constant film.
4. (CURRENTLY AMENDED) The semiconductor device according to claim 1, wherein the semiconductor substrate is a silicon substrate or a silicon layer.
5. (CURRENTLY AMENDED) The semiconductor device according to claim 2, wherein the p-type impurity-contained layer is a boron-contained silicon layer.

Claims 6. – 12. are (CANCELED)

13. (CURRENTLY AMENDED) A semiconductor device comprising:
[[A]] a semiconductor substrate;
a gate insulating film on the semiconductor substrate; and
a gate electrode formed on the gate insulating film and including at least a p-type impurity-contained layer,

wherein the gate insulating film includes a high-dielectric-constant film and a nitride layer on the high-dielectric-constant ~~film~~film, and

wherein the high-dielectric constant film is selected from film comprised of enhanced dielectric materials including Al₂O₃, ZrO₂, HfO₂, and PrO₂, silicate film derived from said enhanced dielectric materials, film having multi-element materials including a combination of at least two of Al₂O₃, ZrO₂, HfO₂, and PrO₂, and film having multi-layered structures including at least two layers of said silicate film.

14. (CURRENTLY AMENDED) The semiconductor device according to ~~claim~~claim 13, wherein the nitride layer is formed by introducing nitrogen into a top surface portion of the high-dielectric-constant film.

15. (CURRENTLY AMENDED) The semiconductor device according to ~~claim~~claim 13, wherein the semiconductor substrate is a silicon substrate or a silicon layer.

16. (CURRENTLY AMENDED) The semiconductor device according to ~~claim~~claim 13, wherein the p-type impurity-contained layer is a boron-contained silicon layer.

Claims 17. – 22. are (CANCELED)